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Variable Range Hopping Conduction in Complex Systems and a Percolation Model with Tunneling

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For the low-temperature electrical conductance of a disordered *quantum insulator* in d-dimensions, Mott [1] had proposed his Variable Range Hopping (VRH) formula, $G(T) = G_0 \exp[-(T_0/T)^\gamma]$, where G_0 is a material constant and T_0 is a characteristic temperature scale. For disordered but non-interacting carrier charges, Mott had found that $\gamma = 1/(d+1)$ in d-dimensions. Later on, Efros and Shkolvskii [2] found that for a pure (*i.e.*, disorder-free) *quantum insulator* with interacting charges, $\gamma = 1/2$, *independent of d*. Recent experiments indicate that γ is either (i) larger than any of the above predictions; and, (ii) more intriguingly, it seems to be a function of p, the dopant concentration. We investigate this issue with a *semi-classical* or *semi-quantum* RRTN (*Random Resistor cum Tunneling-bond Network*) model, developed by us in the 1990's. These macroscopic *granular/percolative composites* are built up from randomly placed meso- or nanoscopic coarse-grained clusters, with two phenomenological functions for the temperature-dependence of the metallic and the semi-conducting bonds. We find that our RRTN model (in 2D, for simplicity) also captures this continuous change of γ with p, satisfactorily.

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The low-temperature *dc* electrical conductance $G(T)$ is being studied for many decades now, in the regime where the thermal energy k_BT (k_B = Boltzmann constant) is of the order of or smaller than the disorder or the Coulomb interaction energy between the charge carrying fermions. In the decade of 1960's, Mott [1] had put forward an analytical expression for the *phonon-assisted hopping* conduction of *spinless fermions*, taking *only the lattice disorder* effect into account and his *Variable Range Hopping* (VRH) formula is written as,

$$G(T) = G_0 \exp\left[-\left(\frac{T_0}{T}\right)^\gamma\right], \qquad (1)$$

where G_0 is a material parameter, $\gamma = 1/(d+1)$ for a d-dimensional sample (e.g., $\gamma = 1/4$ in 3D), and T_0 is a sample-specific temperature scale, below which *quantum mechanical tunneling* between nearby fermionic states (electron or hole), *localized around a finite number of lattice sites*, starts contributing significantly to the $G(T)$ with the help of *hopping* due to phonons. Classically, these regions behave as *finite size clusters*. For a quantum insulator, as T tends to T_0, the *coherent tunneling* process (or, hopping conduction) keeps increasing, while the *incoherent scattering* due to the phonons (or, the ohmic resistance) keeps decreasing. After Mott's seminal work, Efros and Shklovskii [2] considered the localization due *only* to the *repulsive Coulomb interaction* between the charge carriers in a pure system, and achieved the complementary result that $\gamma = 1/2$ for an insulating sample in any d. Musing over both the types of VRH, one may take k_BT_0 as the energy-scale which determines the domain above which incoherent (dephasing) scattering among the localised electron/hole states *completely takes over*, and transforms an Anderson or a Mott insulator into an Ohmic (diffusive) metal. Thus, for a complete description, the VRH formula should take the following *general* form:

$$G(T) = G_0 \left(\frac{T_0}{T}\right)^s \exp\left[-\left(\frac{T_0}{T}\right)^\gamma\right], \qquad (2)$$

as argued by Aharony *et.al.* [3].

But, relatively recently, there have been a few theoretical works (*e.g.*, ref. [4]) and some experiments (*e.g.*, [5, 6, 7]) which do not seem to fall into any of the above schemes, in the sense that the exponent γ is different from the above predictions. While the theory of Ref.[4] predicts $\gamma > 1/4$ in 3D disordered systems on fractal media (due to hopping between *superlocalized* states), and the experiment of Ref.[5] on Carbon black-PVC composites seem to confirm such hoppings in the presence of both disorder and interaction. Here *superlocalized states* are those whose wave-functions decay with the distance R as $\exp[-(R/\xi)^\zeta]$, with $\zeta > 1$; ξ being the localization length. If hopping takes place between superlocalized states, then the Mott VRH was shown to modify the exponent γ in Eq.(1) to $\gamma = d_f/(d_f+\zeta)$, where d_f is the fractal dimension of the medium [4]. Experimental [5] evidence of the above has been reported in carbon-black-polymer composites, where it is claimed that $\zeta = 1.94 \pm 0.06$. However, doubt has been cast by Aharony *et al.* [3] whether the superlocalization was really observed in such composites. As a matter of fact, in the last decade, several experiments (e.g., Ref. [6, 7]) had reported deviations from

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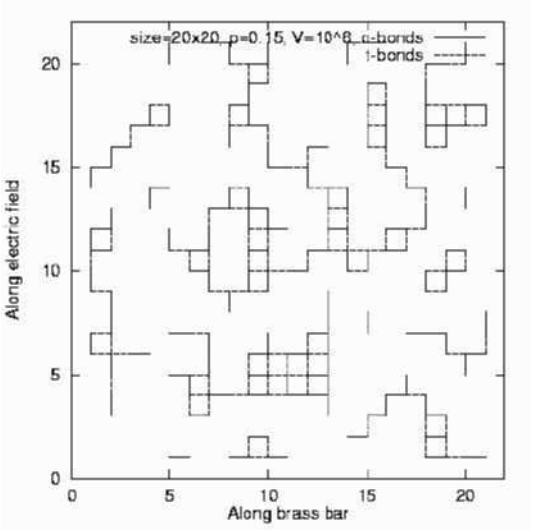


Figure 1: An example of a 20x20 square-lattice configuration in RRTN model, at a random o-bond (full lines) concentration of p=0.15 and with at an arbitrarily high voltage of $10^8 V$, just to make sure that all the t-bonds (dashed lines, with a threshold of $v_g = 0.5V$) are active (with an *inessential* assumption of no Joule heating). One may note here that both the RRN and the RRTN sample is non-percolating (both an insulator).

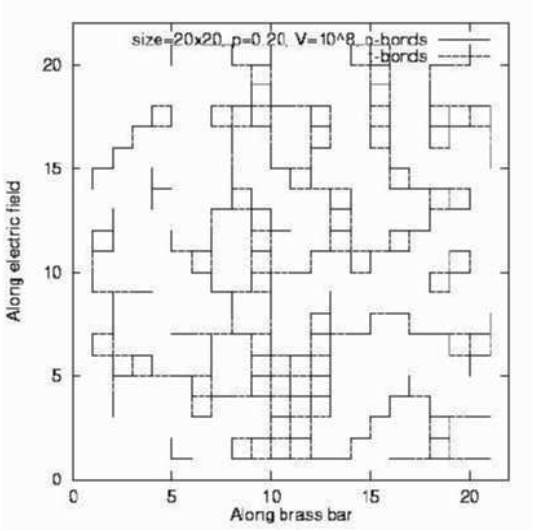


Figure 2: Another example of a 20x20 square lattice configuration (where all the possible t-bonds are driven active) but at a slightly larger p=0.20. Some parts of both the lattices look identical, because their construction started with the same iseed (a trivial issue). One may observe here that the RRTN is percolating (metal) but the RRN is not (insulator). These two Figs. 1 and 2 thus indicate a *new* insulator-metal transition with a percolation threshold inside $0.15 < p < 0.20$.

the above-mentioned results. Indeed, the more serious deviation has been the continuous variation of the exponent γ with the dopant (or, disorder) concentration, p, in some *granular* or *composite* materials. To capture the basic physics of this intriguing behaviour, we undertook a thorough study of the low-temperature conductance in a semi-classical percolation model, called the RRTN (*Random Resistor cum Tunneling-bond Network*) model. The details of the model and some of its applications are discussed in the original papers by Sen and co-workers [8, 9, 10, 11]. Briefly stated, in the RRTN, over and above the randomly placed ohmic (o) bonds in an insulating background, (called a *Random Resistor Network*, or RRN), a *semi-classical tunneling* is allowed *only* through the *nearest-neighbor insulators* between any two o-bonds. Thus, these particular insulating bonds are called tunneling (t) bonds. The placement of these t-bonds in a deterministic way (for a given random resistor configuration) makes our RRTN model partly deterministic (statistically correlated). It may be noted that in the RRTN model, (i) the *disorder*-parameter is introduced through the random occupations of the o-bonds on the lattice, and (ii) the *Coulomb interaction* is mimicked through the *gap* or the threshold voltage v_g for tunneling past the t-bonds. Thus, for a given macroscopic external voltage V, a given t-bond becomes *active* (*i.e.*, lets tunneling take place) if the microscopic voltage difference across its ends is above v_g, and remains inactive if this voltage difference is below v_g. We call the percolation threshold of the RRTN model, when all the possible t-bonds are active, p_{ct}. For the RRTN embedded in a 2D-square lattice, finite-size analysis gives $p_{ct} \simeq 0.181$ (in an Effective Medium Approximation (EMA), p_{ct} is 0.25) [8, 9].

It may be noted that the temperature T does not explicitly appear in any percolation model. So, to study the VRH phenomenon in the RRTN (in a 2D-square lattice), we use some *empirical parameters* for the T-dependence of the *microscopic* conductance of the various types of bonds. For simplicity, for the o-bonds we use $g_o = 1/(r_o + a\,T)$ and for the t-bonds, $g_t = b\,\exp(-c/T)$. To go beyond the EMA, *i.e.*, to study the effects of both the thermal and the (semi)-quantum fluctuations, we had to take recourse to a numerical solution of the Kirchoff's laws (*local current conservation*) at each node of the lattice. The aim is to achieve *global current* (which may be zero if the macroscopic sample is an insulator) *conservation* from the local ones in the RRTN. In a classically percolating situation at a low voltage V, where the ohmic backbone is already percolating, we find a *non-monotonic* sharp rise in the conductance as $T \to 0$; eventuallly saturating to a large but finite *residual resistance* R_0, *i.e.*, $R(T = 0; RRTN)$, in any finite-size RRTN sample. Further, R_0 is found to be *sensitively dependent on specific configurations* (*i.e.*, sample-specific), for any given concentration p of the o-bonds. These findings have, at least, a qualitative matching, with some experimental results on *composite/ granular materials*, as well as those in *fully quantum disordered* systems (*e.g.*, see Ref. [13]). In the Fig.3, we present the T-dependence of the conductance in finite-sized ($L = 20$) RRTN samples for six different p's. Fig.4 shows the excess effect of the

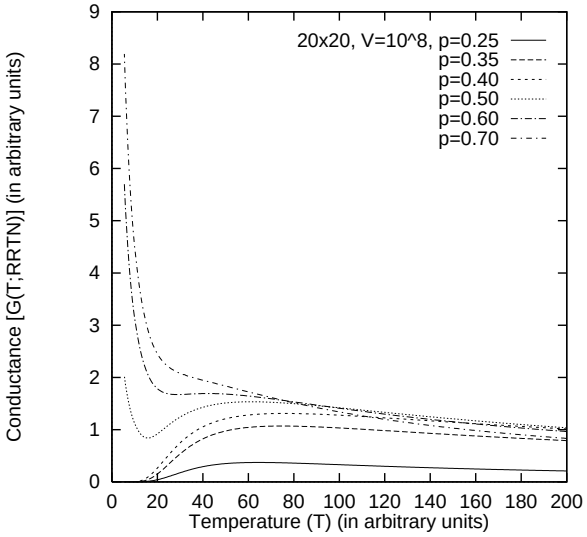


Figure 3: Conductance $G(T)$ *.vs.* temperature T in six 20x20 RRTN square-lattices for various p's in the upper ohmic regime. Due to finite-size effects, some are percolating and some are not.

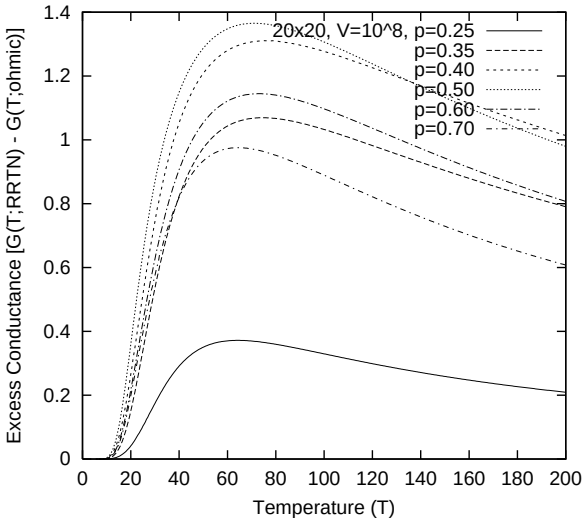


Figure 4: Excess $G(T)$ in the same RRTN samples, as in the Fig.3. The word *excess* means that the ohmic (RRN) part of the $G(T)$ for the percolating RRTN samples at each T is subtracted out.

t-bonds on the same footing for all the samples (both the percolating and the nonpercolating RRTN) of Fig.3, by subtracting their RRN (ohmic) contributions at each T. We calculated the exponents using the *finite size scaling* analysis. In the Fig.5, we show a typical finite size effect on the 2D-RRTN in the *flat upper ohmic regime* (where all the possible t-bonds are active). In our previous study [12] in this regime, the finite-size effects had seemed vanishing. More precise analysis with four L's (see Fig.5 for $T < T_m$) indicate that $\gamma \to 1$ sensitively, but s is very robust ($2.0 < s < 3.0$) as $T \to 0$. Also, this size-effect is stronger in the strongly nonlinear, sigmoidal regime, of

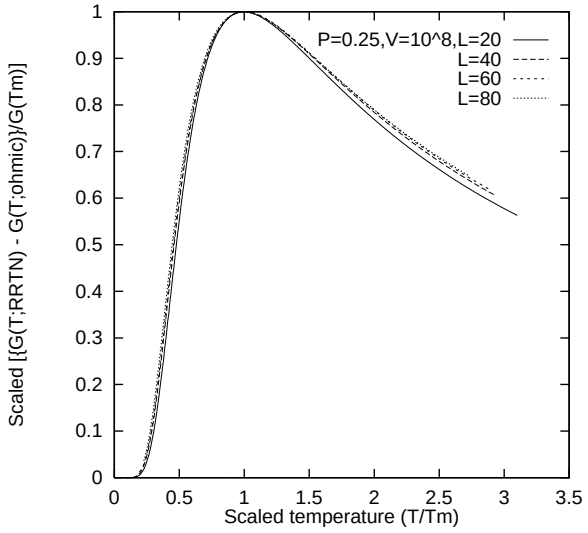


Figure 5: Normalized VRH conductances in the RRTN model at $p = 0.25$ for 2D-square lattices of various sizes, in the limit where all the allowed t-bonds are active. The maxima values $G_m = G(T_m, L)$ and the corresponding $T_m = T_m(L, p)$'s are used to normalize each curve. The fittings of the VRH parameters for each L use the full curves. The finite-size effects are *NOT too prominent* for $T < T_m$.

the *dc* current-voltage response [8, 11]. These details will be discussed elsewhere.

To summarize, we find that our RRTN model is quite successful in describing the VRH and that the *generalized* VRH formula, Eq.(2), works better than the restricted one, *i.e.*, Eq.(1). To wit, the exponents vary continuously with the concentration p of the o-bonds. So, it is capable of reproducing, at least qualitatively, the intriguing results of some recent experiments on (Carbon-black)-(PVC) mixture [5], sulfonated polyaniline (called PANI-CSA) composites [6], some doped Langmuir-Blodgett films [7] etc. Of course, the EMA-values of s and γ differ from their respective numerically "exact" values; *e.g.*, in the EMA, $s = 0.5$ for all the p's. Further theoretical studies would possibly involve the *non-extensivity and some generalized entropy*, defined as a *measure of loss of information*, as formulated by Tsallis' and Re'nyi (see, *e.g.*, ref.[14] by Abe), for the far-from-equilibrium dynamics of the RRTN.

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